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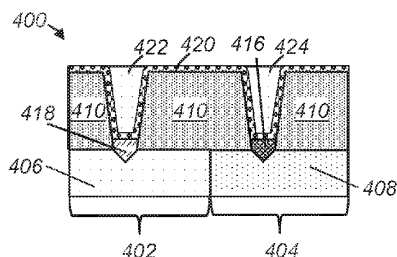


FIG. 4F

(57) Abstract: A method of forming an electrical contact in a semiconductor structure includes performing a cavity shaping process on a semiconductor structures having an n-type metal oxide semiconductor (n-MOS) region and a p-type MOS (p-MOS) region, the cavity shaping process comprising forming an n-MOS cavity in an exposed surface of the n-MOS region and a p-MOS cavity in an exposed surface of the p-MOS region, and performing a first selective deposition process to form a p-MOS cavity contact, selectively in the p-MOS cavity.

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